#### GLA-02 **Low Noise Amplifier Module**

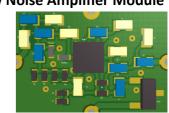


Frequency: 128.23MHz Input impedance :  $0.5\Omega$ 

Noise: 0.4dB Gain: 29dB P<sub>1dB</sub>: 10dBm OIP<sub>3</sub>: 19dBm Output VSMR: 1.2

Magnet free 6V single supply

Applications: MRI, RF telemetry, medical.



#### **Description:**

GLA-02 is a Low Noise Amplifier (LNA) with low input impedance, it is designed to work with  $50\Omega$ source impedance of multi-channel coils, the front end amplifier exhibits superior performance on noise figure. Also, with its wider noise contour map, the front end amplifier can increase its blocked impedance by using higher source impedance design, at the same time, keep its superior signal noise ratio.

**Electrical Characteristics (Ta = 25°C)** 

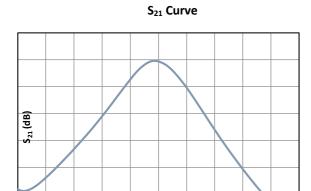
| Symbol           | Parameter                                | Test Conditions   | Value |         | Unit |     |
|------------------|--|---|-------|---------|------|-----|
|                  |  |   | Min   | Typical | Max  |     |
| S <sub>21</sub>  | Gain                                     | 128.23 MHz  | 29    | 29.5    | 30   | dB  |
| $\DeltaG$        | Gain Variation                           | 128.23 MHz $\pm$ 1MHz                                       | -     | -       | ±0.1 | dB  |
| RE[Zin]          | Input Impedance                          | 128.23 MHz  | 0.5   | 0.55    | 0.6  | Ω   |
| IM[Zin]          |  | 128.23 MHz  | -2    | 0       | 2    | Ω   |
| SWR <sub>2</sub> | Output VSMR                              | 128.23 MHz  | •     | -       | 1.2  | -   |
| S <sub>12</sub>  | Reverse Isolation                        | 128.23 MHz  | 63    | 70      | •    | dB  |
| NF               | Noise Figure                             | 128.23 MHz  | •     | 0.35    | 0.45 | dB  |
| P <sub>1dB</sub> | Output Power at 1dB<br>Compression Point | 63.87 MHz   | 9.5   | 10      | -    | dBm |
| OIP <sub>3</sub> | 3 dB Point Output                        | Each signal channel P <sub>out</sub> = OdBm, 1MHz isolation | 18    | 19.5    | -    | dBm |
| I <sub>dd</sub>  | Consumption Current                      | V <sub>dd</sub> = 6V  |       | 23      | 25   | mA  |
| $V_{dd}$         | Supply Operating Voltage                 |   | 5.9   | 6       | 30   | V   |

Absolute Maximum Ratings (Ta = 25°C)

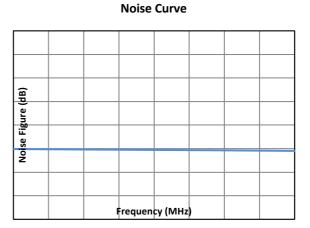
| Parameter             | Unit | Value        | Remark |  |  |  |  |
|-----------------------|------|--------------|--------|--|--|--|--|
| Supply Voltage        | V    | +30V         |        |  |  |  |  |
| Input Signal Power    | dBm  | 15dBm        |        |  |  |  |  |
| Operating Temperature | °C   | -55 ~ +125°C |        |  |  |  |  |
| Sintering Temperature | °C   | -40 ~ +150°C |        |  |  |  |  |
| Storage Temperature   | °C   | -65 ~ +150°C |        |  |  |  |  |

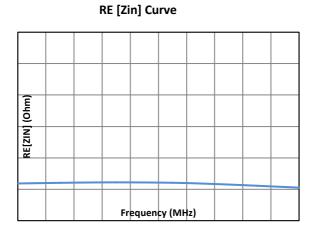
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

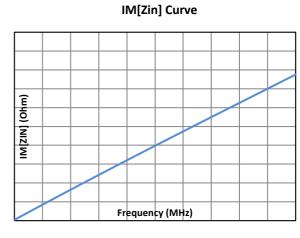
# **Typical Performance**

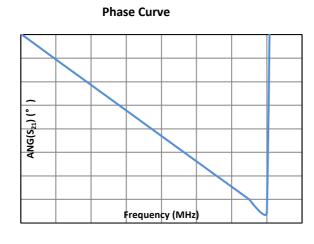


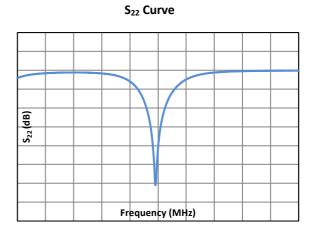
Frequency (MHz)

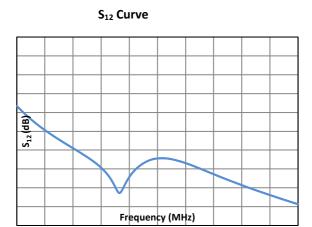


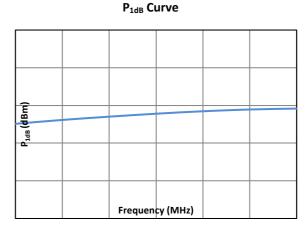


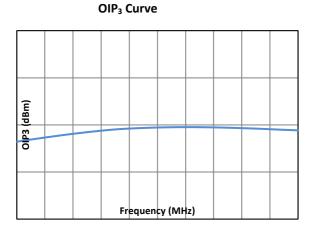


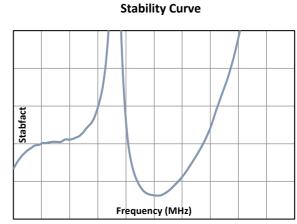




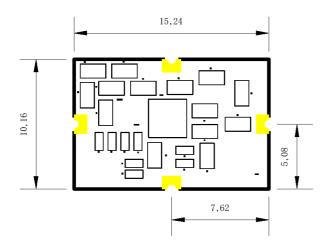


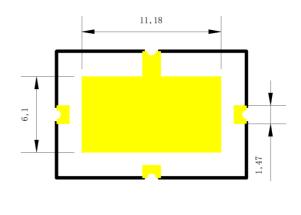




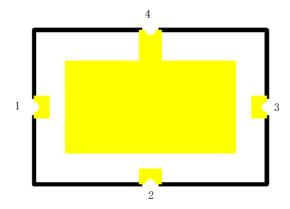


### Chip Dimensions (Unit: µm)





# **Chip Layout Diagram**



| Lead | 1  | 2           | 3             | 4   |  |
|------|----|-------------|---------------|-----|--|
| Use  | IN | $NC/V_{dd}$ | OUT/ $V_{dd}$ | GND |  |